

**isc Silicon NPN Power Transistor**
**2SD552**
**DESCRIPTION**

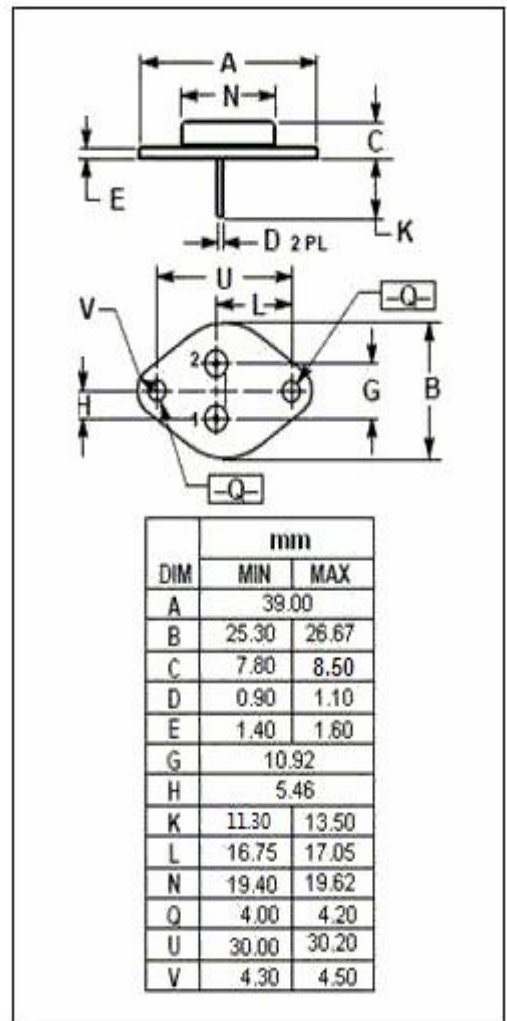
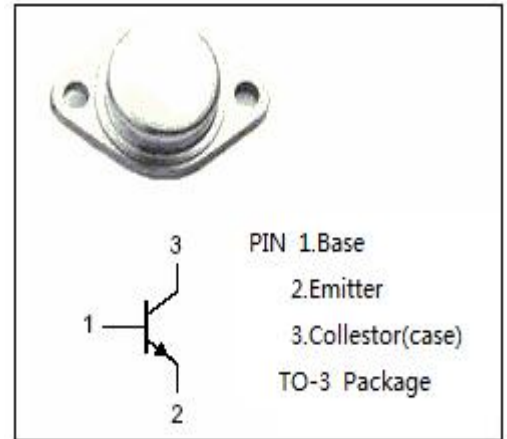
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 180V$  (Min)
- High Power Dissipation
- Complement to Type 2SB552
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Power amplifier, power switching applications.
- DC-DC converter and regulator applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

SYMBOL	PARAMETER	MAX	UNIT
$V_{CBO}$	Collector-Base Voltage	220	V
$V_{CEO}$	Collector-Emitter Voltage	180	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	15	A
$I_E$	Emitter Current-Continuous	15	A
$I_B$	Base Current-Continuous	3	A
$P_C$	Collector Power Dissipation @ $T_c = 25^\circ C$	150	W
$T_j$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ C$



## isc Silicon NPN Power Transistor

## 2SD552

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; R <sub>BE</sub> = 0	180			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	220			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A		1.5	2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	25		80	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 15A; V <sub>CE</sub> = 5V	10	15		
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 50V; f <sub>test</sub> = 1.0MHz		160		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V		4		MHz

## Switching Times

t <sub>on</sub>	Turn-On Time	V <sub>CC</sub> = 125V; R <sub>L</sub> = 25Ω; I <sub>B1</sub> = I <sub>B2</sub> = 0.5A		1	2	μs
t <sub>s</sub>	Storage Time			3.5	7	μs
t <sub>f</sub>	Fall Time			0.5	1	μs

◆ h<sub>FE-1</sub> Classifications

BN	R
25-50	40-80

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